

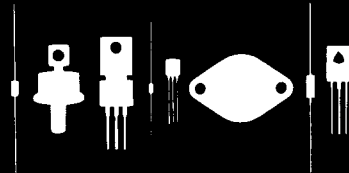
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145 Adams Avenue  
Hauppauge, New York 11788



1N949

GERMANIUM DIODE

JEDEC DO-7 CASE

#### DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N949 type is a gold bonded germanium diode mounted in a hermetically sealed glass case, designed for general purpose applications. Special devices with a higher breakdown voltage and/or lower leakage limits are available on special order.

#### MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ )

	<u>SYMBOL</u>		<u>UNIT</u>
Peak Repetitive Reverse Voltage	$V_{RRM}$	50	V
D.C. Forward Current	$I_F$	100	mA
Peak Forward Current	$I_{FM}$	350	mA
Peak Forward Surge Current (1.0s)*	$I_{FSM}$	500	mA
Power Dissipation**	$P_D$	80	mW
Operating and Storage Junction Temperature	$T_J, T_{STG}$	-65 TO +100	$^\circ\text{C}$

\*Non-recurrent

\*\*Derate above  $25^\circ\text{C}$  10mW/ $10^\circ\text{C}$

#### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNIT</u>
$I_R$	$V_R=10\text{V}$		10	$\mu\text{A}$
$I_R$	$V_R=10\text{V}, T_A=55^\circ\text{C}$		50	$\mu\text{A}$
$BV_R$	$I_R=1.0\text{mA}$	50		V
$V_F$	$I_F=10\text{mA}$		0.42	V
$V_F$	$I_F=200\text{mA}$		1.0	V

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